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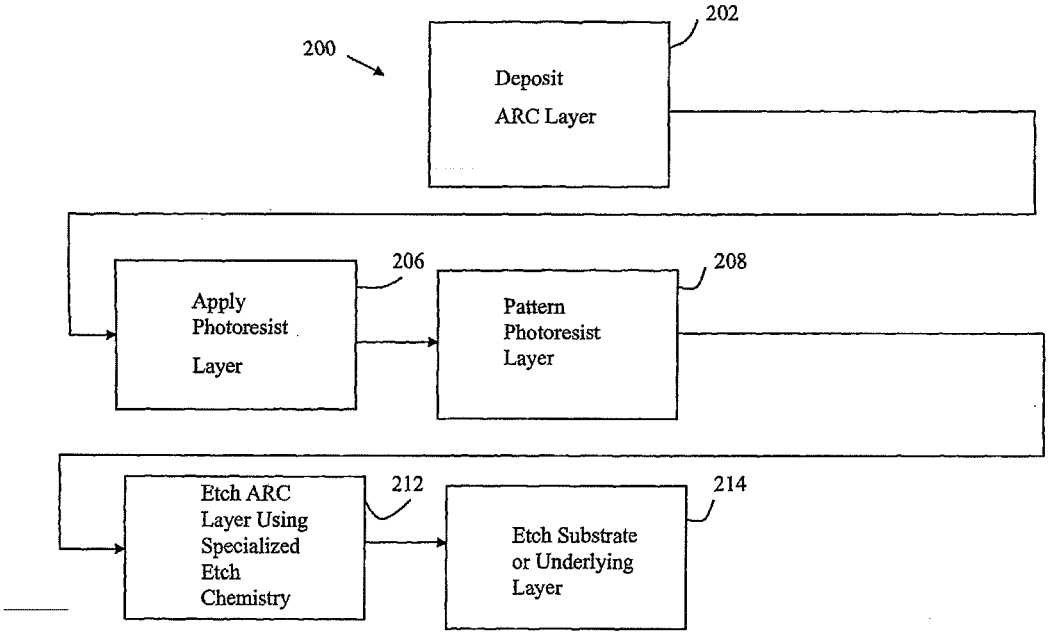
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(54) Title: ETCH PROCESS FOR CD REDUCTION OF ARC MATERIAL



(57) Abstract: A method of reducing critical dimensions of a feature (56, 57, 59) in a anti-reflective coating layer structure (19) can utilize a polymerizing agent. The anti-reflective coating structure can be utilized to form various integrated circuit structures. The anti-reflective coating can be utilized to form gate stacks comprised of polysilicon (54) and a dielectric layer (52), conductive lines (84), or other IC structure. The polymerizing agent can include carbon, hydrogen and fluorine.

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